

of barium atoms located on said surface of said substrate material.

Q2
Counsel
22. A semiconductor device comprising:
a substrate;
a barrier film comprised of a layer of elemental barium atoms on said substrate; and
a material on said barrier film.

23. A semiconductor device comprising:
a substrate;
a barrier film comprising barium atoms having a thickness less than 100Å on said substrate; and
a material on said barrier film. --

REMARKS

Prior to examination, applicants request that the Examiner enter the foregoing amendment to the claims. An early action on the merits is respectfully requested.

Respectfully submitted,

Date: July 7, 1999

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